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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
10/038,990	01/04/2002	Seung-Ki Joo	069457.0106 9637		
75	11/04/2002				
Jay B. Johnson, Esq.			EXAMINER		
Baker Botts L.L.P. Suite 600			LE, THAO X		
2001 Ross Avenue Dallas, TX 75201-2980			ART UNIT PA		
			2814		
			DATE MAILED: 11/04/2002		

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary		10/038,990	JOO ET AL.	N/ /			
		Examiner	Art Unit	7			
		Thao X Le	2814				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply							
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). Status							
1)[Responsive to communication(s) filed on 04 J	lune 2002 .					
2a)□		is action is non-final.					
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.							
Disposition of Claims 4)⊠ Claim(s) <u>1-15</u> is/are pending in the application.							
4) Of the above claim(s) 11-15 is/are withdrawn from consideration.							
5) Claim(s) is/are allowed.							
6)⊠ Claim(s) <u>1-10</u> is/are rejected.							
7)☐ Claim(s) is/are objected to.							
·	Claim(s) are subject to restriction and/or	election requirement.					
Application Papers							
9)⊠ The specification is objected to by the Examiner.							
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.							
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).							
11) The proposed drawing correction filed on is: a) approved b) disapproved by the Examiner.							
If approved, corrected drawings are required in reply to this Office action.							
12) The oath or declaration is objected to by the Examiner.							
_	Priority under 35 U.S.C. §§ 119 and 120						
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).							
a)⊠ All b)□ Some * c)□ None of:							
1. Certified copies of the priority documents have been received.							
}	2. Certified copies of the priority documents						
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).							
 a) ☐ The translation of the foreign language provisional application has been received. 15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121. 							
Attachment	r(s)	•					
2) D Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal	y (PTO-413) Paper Patent Application (
U.S. Patent and Tr	arlemark Office						

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DETAILED ACTION

Election/Restrictions

- 1. Restriction to one of the following inventions is required under 35 U.S.C. 121:
 - I. Claims 1-10, drawn to a method of making a semiconductor device, classified in class 438, subclass 480+.
 - II. Claims 11-15, drawn to an apparatus of making a semiconductor device, classified in class 257, subclass 55, 60-70, 72.

The inventions are distinct, each from the other because of the following reasons:

Inventions Group I and Group II are related as process and apparatus for its practice. The inventions are distinct if it can be shown that either: (1) the process as claimed can be practiced by another materially different apparatus or by hand, or (2) the apparatus as claimed can be used to practice another and materially different process. (MPEP § 806.05(e)). In this case the apparatus as claimed can be used to practice another and materially different process. For example, '...heating substrate..' in claim 1 can be done first, then depositing the metal layer...'.

Because these inventions are distinct for the reasons given above and have acquired a separate status in the art as shown by their different classification, restriction for examination purposes as indicated is proper.

2. During a telephone conversation with Applicant Attorney, Mr. Jay Johnson, on 24 Oct. 02 a provisional election was made WITHOUT traverse to prosecute the invention of Group I, claims1-10. Affirmation of this election must be made by applicant in replying to this Office

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action. Claims 11-15 are withdrawn from further consideration by the examiner, 37 CFR 1.142(b), as being drawn to a non-elected invention.

Applicant is reminded that upon the cancellation of claims to a non-elected invention, the inventorship must be amended in compliance with 37 CFR 1.48(b) if one or more of the currently named inventors is no longer an inventor of at least one claim remaining in the application. Any amendment of inventorship must be accompanied by a request under 37 CFR 1.48(b) and by the fee required under 37 CFR 1.17(i).

Specification

3. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. Claims 1-10 are rejected under 35 U.S.C. 103(a) as being unpatentable over US Pub2001/0034088 to Nakamura et al. in view of US 4908334 to Zuhe et al.

Regarding to claims 1, 3, 10 Nakamura discloses a method of fabricating a semiconductor device including a crystallized active layer comprising the steps of: providing a substrate 10101, fig. 1A, depositing an amorphous silicon (a-Si) layer 10102 layer on substrate,

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depositing a metal layer inducing low temperature crystallization of amorphous silicon on at least a portion of amorphous silicon layer, fig. 1B, [0007] and [0008], wherein the method further comprises forming an insulation layer 10104, fig. 1B on substrate and –Si layer, removing a portion of insulation layer to exposed a portion of a-Si layer.

But, Nakamura does not expressly disclose heating substrate while depositing a metal layer.

However, Zuhr reference discloses heating substrate while depositing a metal layer, column 1 line 10-16 to at a temperature in a range of 200-700°C, column 4 line 21,. At the time the invention was made; it would have been obvious to one of ordinary skill in the art to use the heating substrate while depositing a metal layer teaching of Zuhr with Nakamura, because it would have provided the silicon atoms necessary for forming the stoichiometric metallic silicide as taught by Zuhr, column 4 line 11-17.

Regarding to claims 2, 4, 5 and 7-9, Nakamura discloses the method wherein the metal layer includes at least on element among the group of Ni [0007], , wherein the metal layer is deposited using heat evaporation, [0053] and [0054], wherein the substrate is heated conduction, [0008], wherein the method further comprises a step of removing the remaining metal, [0010], wherein the a-Si layer is crystallized by MIC, [0007], wherein the method further comprises a step of crystallizing a-Si layer by conducting a thermal treatment after depositing metal, [0008]

Regarding to claim 6, Nakamura does not expressly disclose the method wherein the substrate a portion of metal layer contact with a-Si layer formed a metal silicide. It would have been obvious for Ni reacting with silicon to form Ni silicide, such reaction is disclosed by Zuhr.

Conclusion

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6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thao X Le whose telephone number is 703-306-0208. The examiner can normally be reached on M-f from 8:00 AM - 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M Fahmy can be reached on 703-308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Thao X. Le October 25, 2002

> PHAT X. CAO PRIMARY EXAMINER